Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I_{CM}	3	A
Continuous Collector Current	I_C	2	A
Peak Base Current	I_{BM}	0.3	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

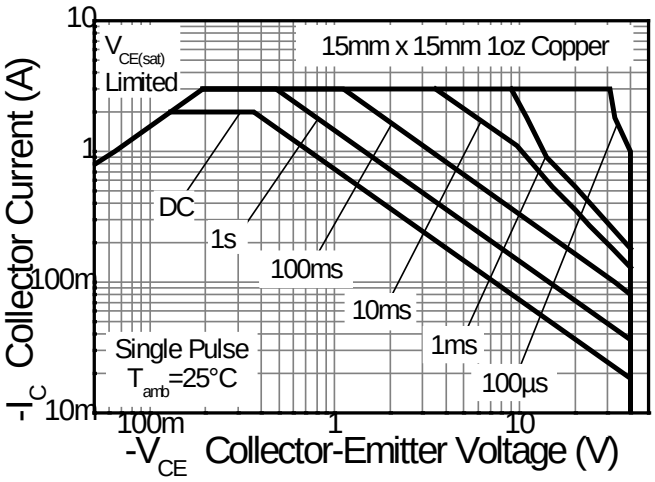
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	730	mW
Power Dissipation (Note 7)	P_D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\Theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	$R_{\Theta JA}$	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	$R_{\Theta JL}$	75	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 9)

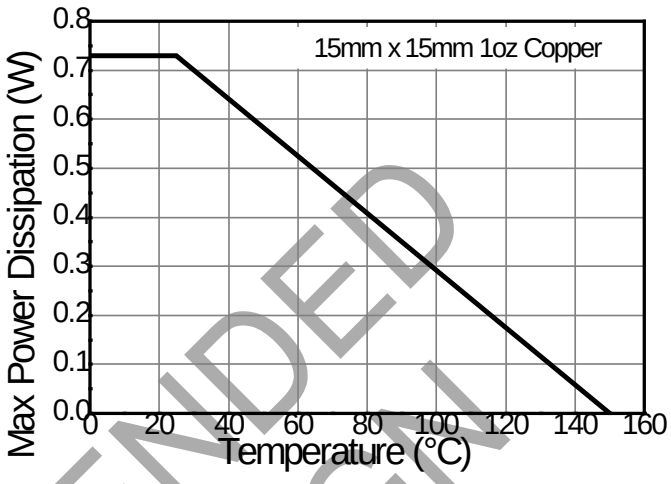
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	C

Notes:
6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as Note 5, except the device is mounted on minimum recommended pad layout.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

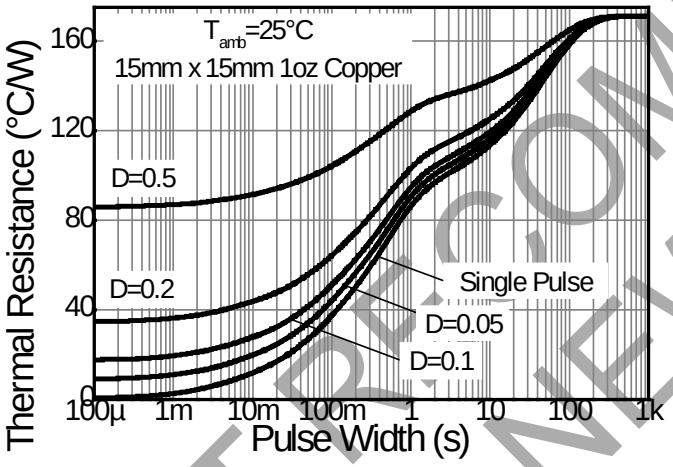
Thermal Characteristics and Derating Information



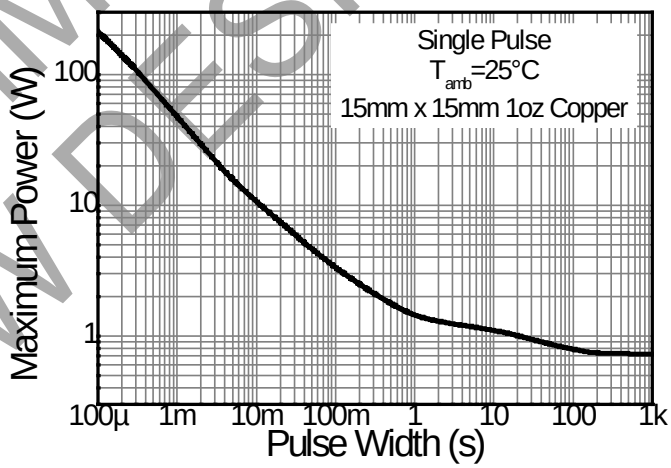
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	40	—	—	V	I_C = 100µA
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	40	—	—	V	I_C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	I_E = 100µA
Collector-Base Cutoff Current	I_{CBO}	—	—	100	nA	V_{CB} = 30V, I_E = 0
		—	—	50	µA	V_{CB} = 30V, I_E = 0, T_A = +150°C
Emitter-Base Cutoff Current	I_{EBO}	—	—	100	nA	V_{EB} = 4V, I_C = 0
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h_{FE}	350	—	—	—	V_{CE} = 2V, I_C = 0.1A
		300	—	—		V_{CE} = 2V, I_C = 0.5A
		300	—	—		V_{CE} = 2V, I_C = 1A
		150	—	—		V_{CE} = 2V, I_C = 2A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	70	mV	I_C = 100mA, I_B = 1mA
		—	30	100		I_C = 500mA, I_B = 50mA
		—	—	180		I_C = 750mA, I_B = 15mA
		—	—	180		I_C = 1A, I_B = 50mA
		—	—	320		I_C = 2A, I_B = 200mA
Equivalent On-Resistance	$R_{CE(sat)}$	—	60	200	mΩ	I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	1.1	V	I_C = 2A, I_B = 200mA
Base-Emitter Turn-on Voltage	$V_{BE(on)}$	—	—	0.75	V	V_{CE} = 2V, I_C = 100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	100	—	—	MHz	V_{CE} = 10V, I_C = 100mA, f = 100MHz
Output Capacitance	C_{ob}	–	—	20	pF	V_{CB} = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

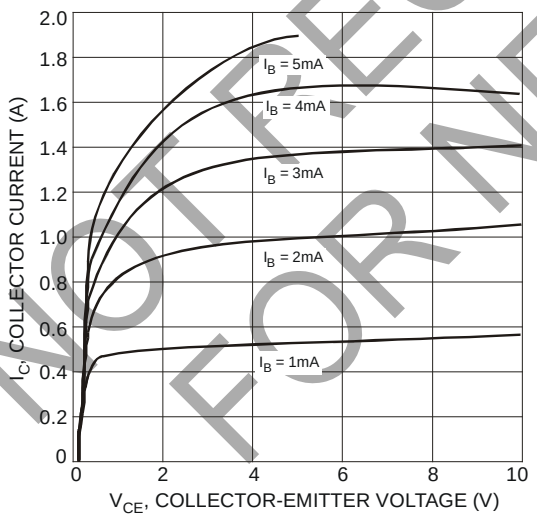


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

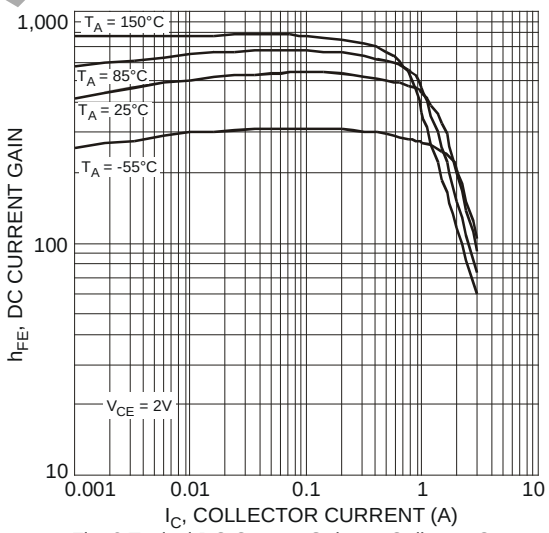


Fig. 3 Typical DC Current Gain vs. Collector Current

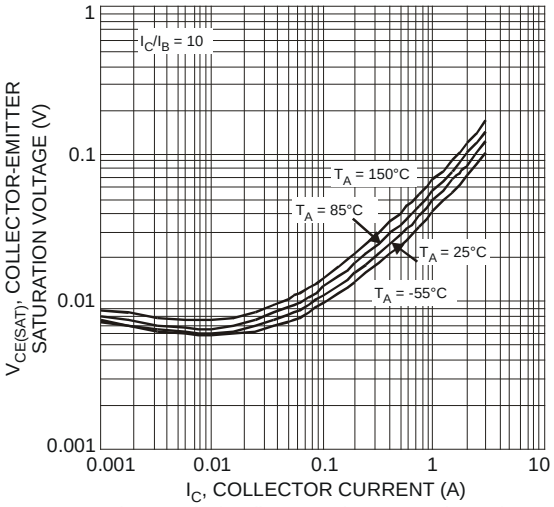


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

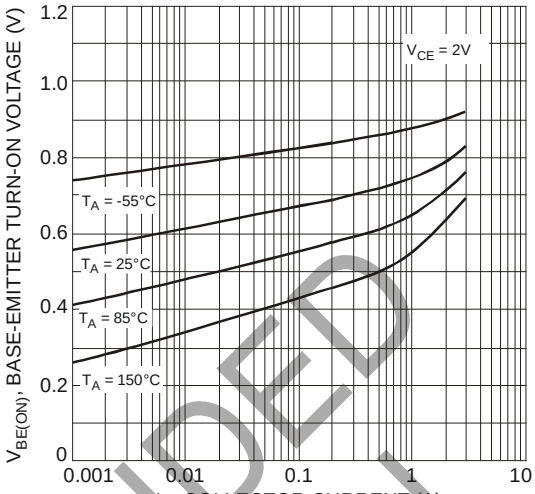


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

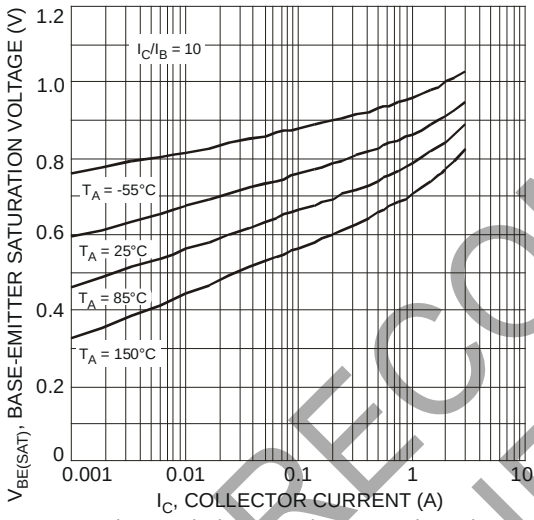


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

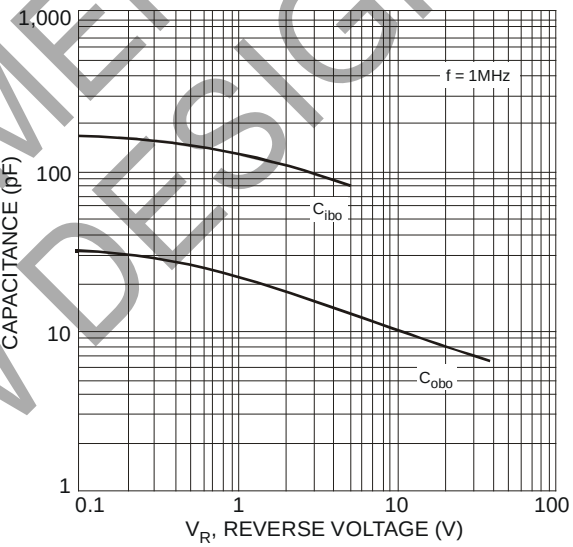


Fig. 7 Typical Capacitance Characteristics

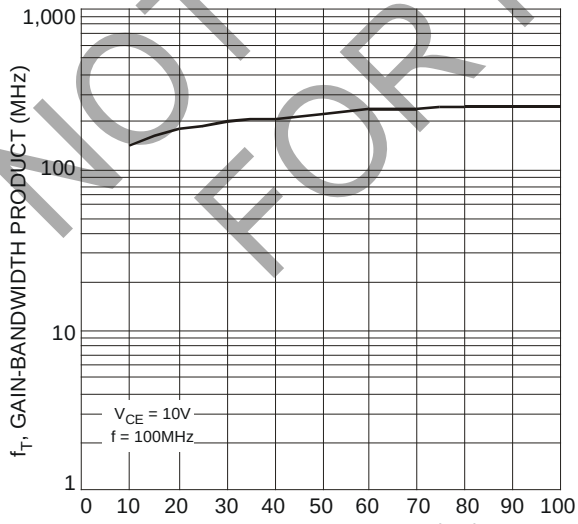
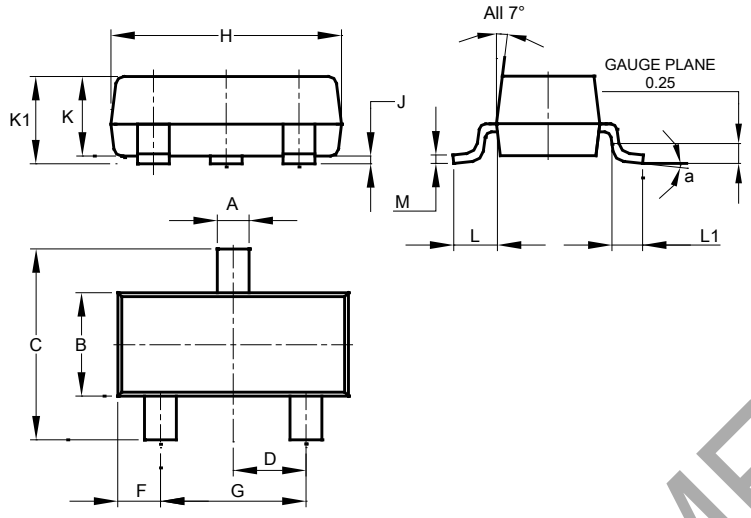


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

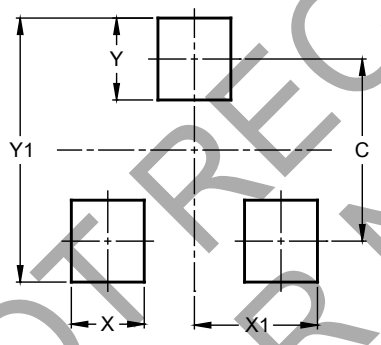


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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